

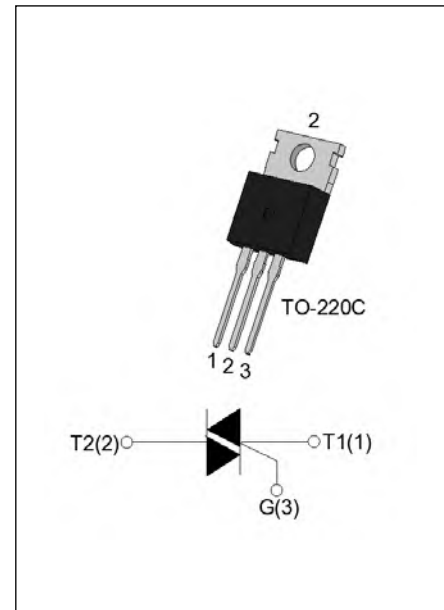
BT139-800E

DESCRIPTION:

The BT139-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	10/10/10/25	mA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	℃
Operating junction temperature range		T _j	-40-125	℃
Repetitive peak off-state voltage (T _j =25℃)		V _{DRM}	800	V
Repetitive peak reverse voltage (T _j =25℃)		V _{RRM}	800	V
RMS on-state current (T _c ≤95℃)		I _{T(RMS)}	16	A
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25℃)		I _{TSM}	140	A
Non repetitive surge peak on-state current (full cycle , t _p =16.6ms , T _j =25℃)			154	
I ² t value for fusing (t _p =10ms , T _j =25℃)		I ² t	98	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT} , f=100Hz , T _j =125℃)	I - II	di/dt	80	A/μs
	III-IV		50	
Peak gate current (t _p =20μs , T _j =125℃)		I _{GM}	4	A
Average gate power dissipation (T _j =125℃)		P _{G(AV)}	0.5	W
Peak gate power		P _{GM}	10	W
Peak pulse voltage (T _j =25℃; non-repetitive,off-state;FIG.7)		V _{pp}	4.5	kV

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ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX.	10	mA
		IV		25	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III - IV	MAX.	25	mA
		II		35	
I _H	I _T =500mA		MAX.	25	mA
dV/dt	V _D =540V Gate Open T _j =125°C		MIN.	100	V/μs
(dV/dt) _c	(dI/dt) _c =7.2A/ms, T _j =110°C		MIN.	5	V/μs
t _{on}	I _G =40mA I _A =200mA I _R =20mA T _j =25°C		TYP.	3	μs
t _{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =20A t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.75	V
R _D	Dynamic resistance	T _j =125°C	27	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25°C	5	μA
I _{RRM}		T _j =125°C	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	1.3	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W

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FIG.1 Maximum power dissipation versus RMS on-state current

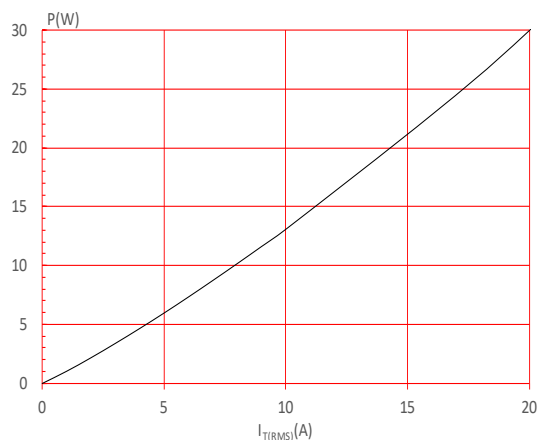


FIG.3: Surge peak on-state current versus number of cycles

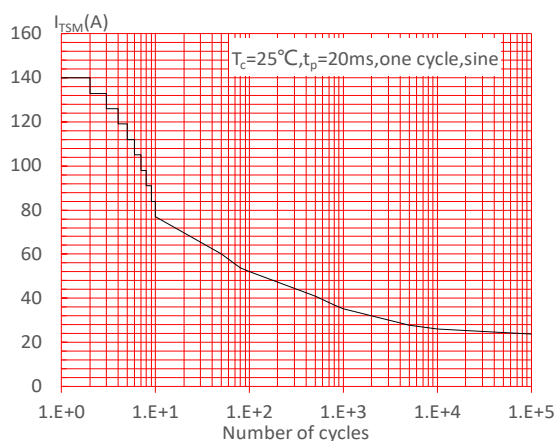


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t
(I - II: $di/dt < 80\text{A}/\mu\text{s}$; III-IV: $di/dt < 50\text{A}/\mu\text{s}$)

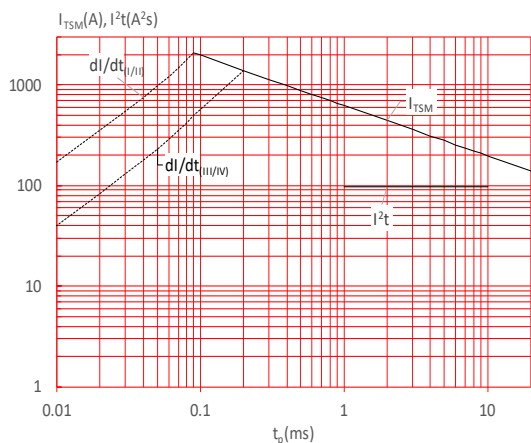


FIG.2: RMS on-state current versus case temperature

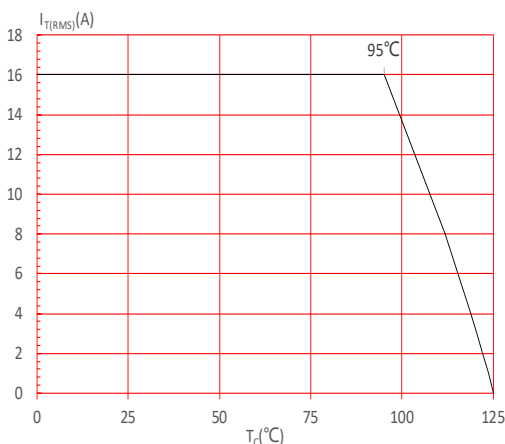


FIG.4: On-state characteristics

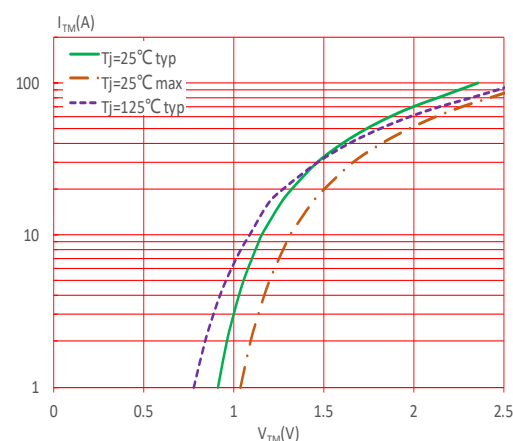
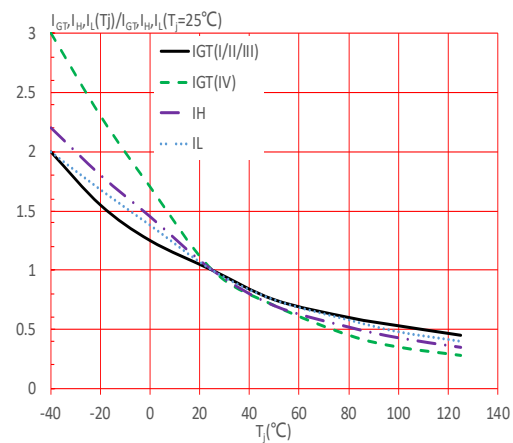
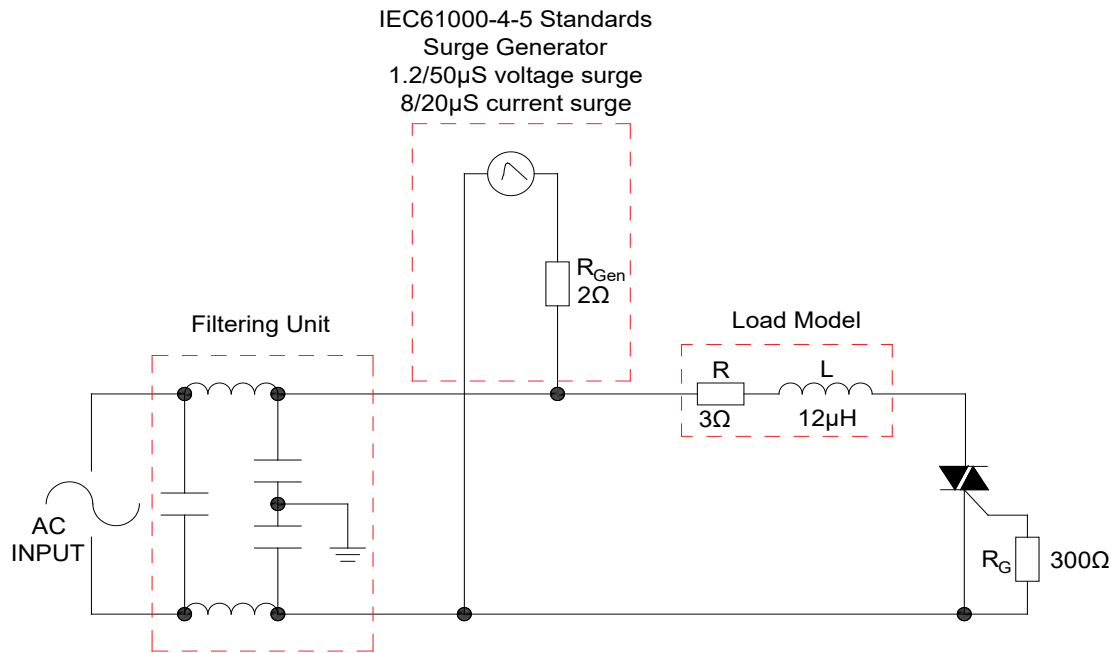


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



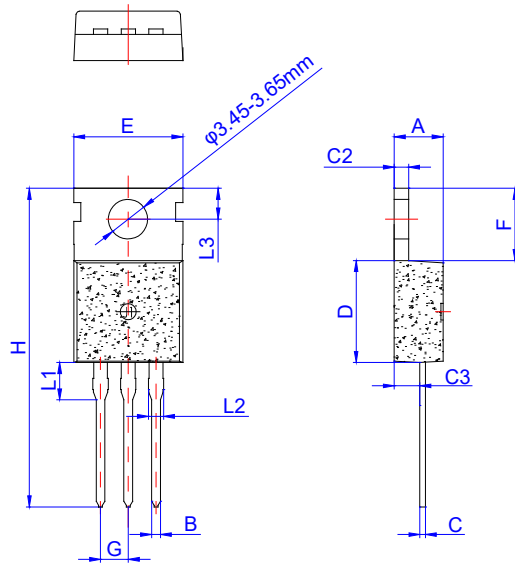
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FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE

